# SKKT 273; SKKH 273



SEMIPACK<sup>®</sup> 3

Thyristor / Diode Modules

#### SKKT 273 SKKH 273

### Features

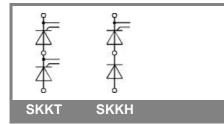
- Industrial standard package
- Electrically insulated base plate
- Heat transfer through aluminum
- oxide ceramic insulated metal base plate
- Chip soldered on direct copper bonded Al<sub>2</sub>O<sub>3</sub> ceramic
- Thyristor with center gate
- UL recognition applied for file no. E63532

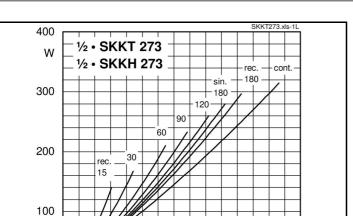
### **Typical Applications\***

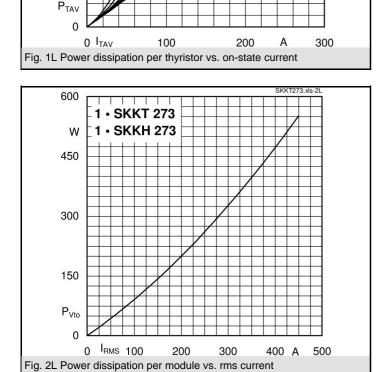
- DC motor control
  (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)
- 1) See the assembly instructions

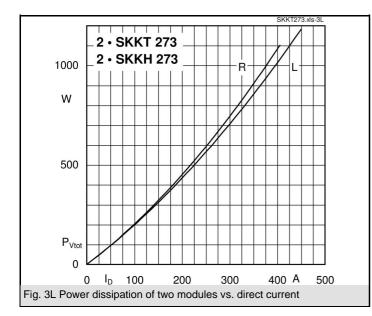
| V <sub>RSM</sub> | $V_{RRM}, V_{DRM}$ | I <sub>TRMS</sub> = 450 A (maximum value for continuous operation) |              |  |
|------------------|--------------------|--|--------------|--|
| V                | V                  | I <sub>TAV</sub> = 273 A (sin. 180; T <sub>c</sub> = 85 °C)        |              |  |
| 1300             | 1200               | SKKT 273/12E   | SKKH 273/12E |  |
| 1700             | 1600               | SKKT 273/16E   | SKKH 273/16E |  |
| 1900             | 1800               | SKKT 273/18E   | SKKH 273/18E |  |

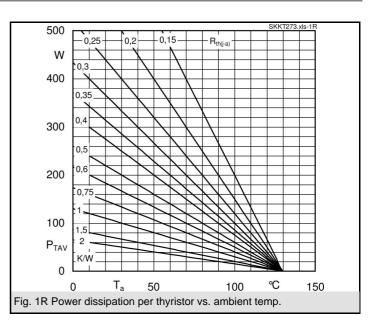
| Symbol                            | Conditions  | Values                 | Units |
|-----------------------------------|---|------------------------|-------|
| I <sub>TAV</sub>                  | sin. 180; T <sub>c</sub> = 85 (100) °C;                                     | 273 (202 )             | А     |
| I <sub>TSM</sub>                  | T <sub>vi</sub> = 25 °C; 10 ms  | 9000                   | А     |
|                                   | T <sub>vj</sub> = 130 °C; 10 ms   | 8000                   | А     |
| i²t                               | T <sub>vj</sub> = 25 °C; 8,3 10 ms  | 405000                 | A²s   |
|                                   | T <sub>vj</sub> = 130 °C; 8,3 10 ms   | 320000                 | A²s   |
| V <sub>T</sub>                    | T <sub>vi</sub> = 25 °C; I <sub>T</sub> = 750 A                             | max. 1,6               | V     |
| V <sub>T(TO)</sub>                | T <sub>vi</sub> = 130 °C  | max. 0,9               | V     |
| r <sub>T</sub>                    | $T_{vi} = 130 \ ^{\circ}C$  | max. 0,92              | mΩ    |
| I <sub>DD</sub> ; I <sub>RD</sub> | $T_{vj} = 130 \text{ °C}; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$               | max. 100               | mA    |
| t <sub>gd</sub>                   | T <sub>vi</sub> = 25 °C; I <sub>G</sub> = 1 A; di <sub>G</sub> /dt = 1 A/µs | 1                      | μs    |
| t <sub>gr</sub>                   | $V_{\rm D} = 0.67 * V_{\rm DRM}$  | 2                      | μs    |
| (di/dt) <sub>cr</sub>             | T <sub>vi</sub> = 130 °C  | max. 130               | A/µs  |
| (dv/dt) <sub>cr</sub>             | $T_{vi}^{3} = 130 \ ^{\circ}C$  | max. 1000              | V/µs  |
| t <sub>q</sub>                    | $T_{vi}^{(1)} = 130 \ ^{\circ}C$ , typ.                                     | 150                    | μs    |
| I <sub>H</sub>                    | $T_{vi}^{,j}$ = 25 °C; typ. / max.  | 150 / 500              | mA    |
| IL .                              | T <sub>vi</sub> = 25 °C; R <sub>G</sub> = 33 Ω; typ. / max.                 | 300 / 2000             | mA    |
| V <sub>GT</sub>                   | T <sub>vi</sub> = 25 °C; d.c.   | min. 2                 | V     |
| I <sub>GT</sub>                   | T <sub>vi</sub> = 25 °C; d.c.   | min. 150               | mA    |
| V <sub>GD</sub>                   | T <sub>vj</sub> = 130 °C; d.c.  | max. 0,25              | V     |
| I <sub>GD</sub>                   | T <sub>vj</sub> = 130 °C; d.c.  | max. 10                | mA    |
| R <sub>th(j-c)</sub>              | cont.; per thyristor / per module   | 0,104 / 0,052          | K/W   |
| R <sub>th(j-c)</sub>              | sin. 180; per thyristor / per module  | 0,108 / 0,054          | K/W   |
| R <sub>th(j-c)</sub>              | rec. 120; per thyristor / per module  | 0,122 / 0,061          | K/W   |
| R <sub>th(c-s)</sub>              | per thyristor / per module  | 0,08 / 0,04            | K/W   |
| T <sub>vi</sub>                   |   | - 40 + 130             | °C    |
| T <sub>stg</sub>                  |   | - 40 + 125             | °C    |
| V <sub>isol</sub>                 | a. c. 50 Hz; r.m.s.; 1 s / 1 min.   | 3600 / 3000            | V~    |
| Ms                                | to heatsink   | 5 ± 15 % <sup>1)</sup> | Nm    |
| Mt                                | to terminals  | 9 ± 15 %               | Nm    |
| a                                 |   | 5 * 9,81               | m/s²  |
| m                                 | approx.   | 410                    | g     |
| Case                              | SKKT  | A 43a                  |       |
|                                   | SKKH  | A 56a                  |       |

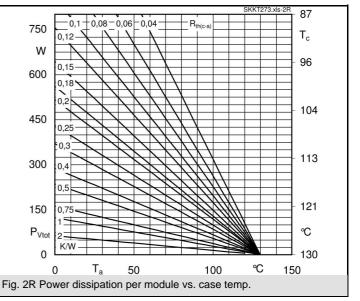


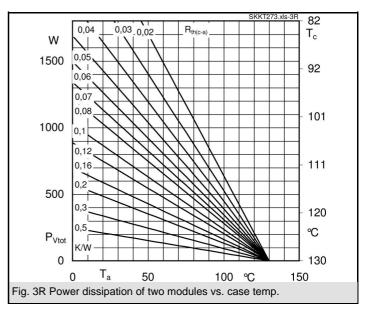




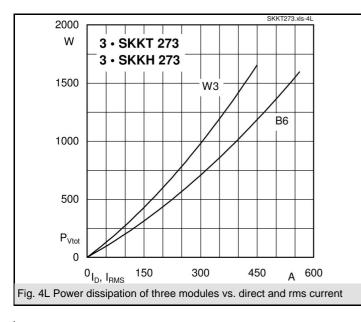


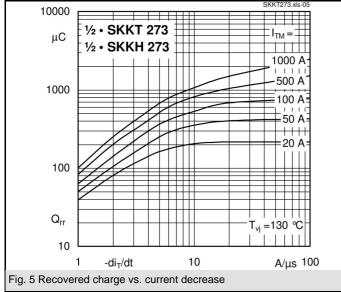


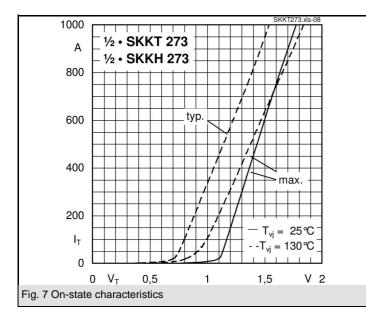


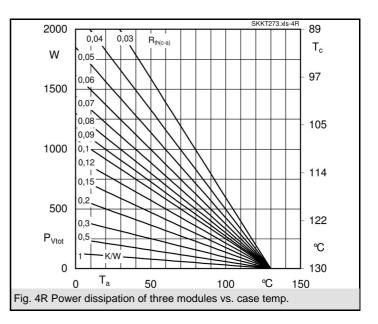


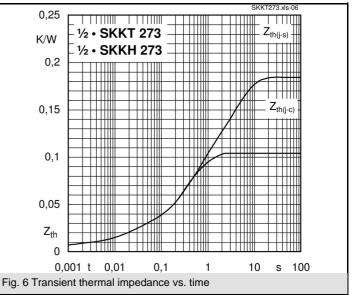
## SKKT 273; SKKH 273

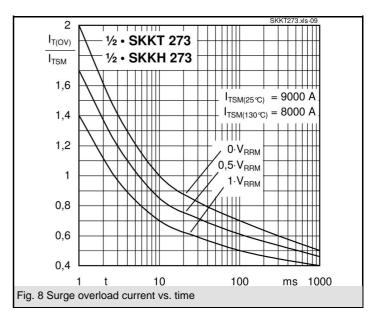


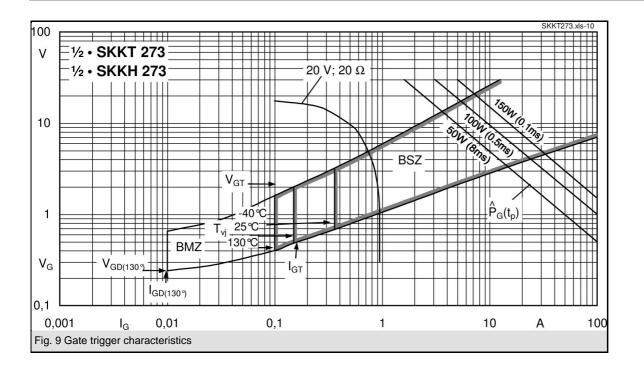


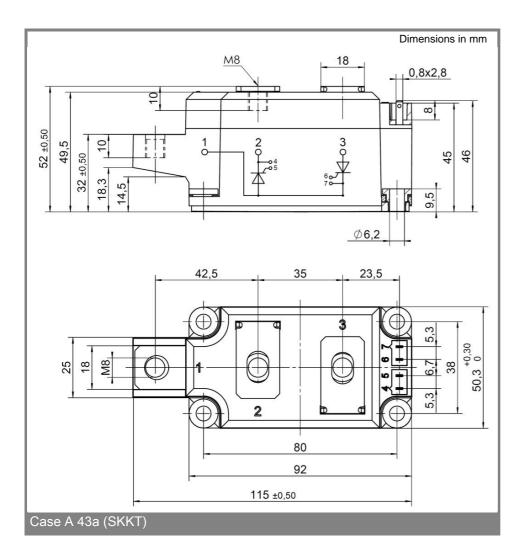




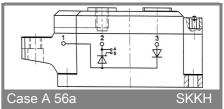








4



\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We

# SKKT 273; SKKH 273

therefore strongly recommend prior consultation of our staff.